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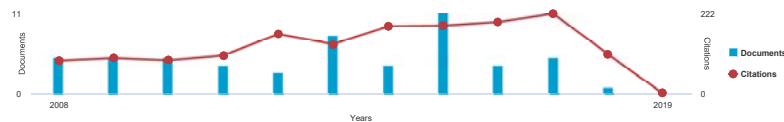
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Electrical & Computer Engineering, Singapore
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